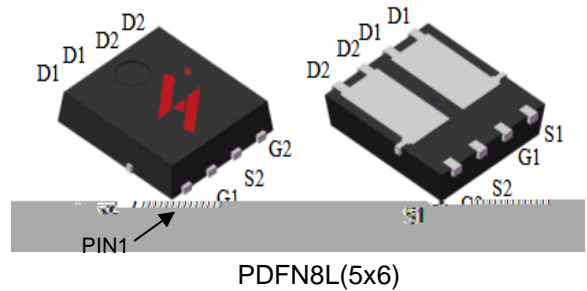


Dual N-Channel Enhancement Mode MOSFET

Feature

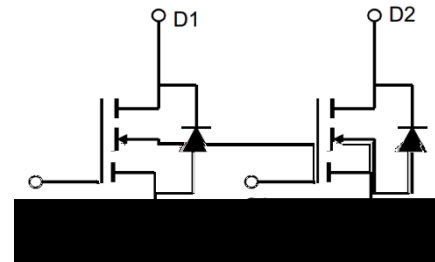
- 60V/56A
- $R_{DS(ON)} = 8.0\text{ m}\Omega$ (typ.) @ $V_{GS} = 10\text{V}$
- $R_{DS(ON)} = 12.2\text{ m}\Omega$ (typ.) @ $V_{GS} = 4.5\text{V}$
- 100% Avalanche Tested
- Reliable and Rugged
- Halogen Free and Green Devices Available (RoHS Compliant)

Pin Description



Applications

- Switching Application
- Power Management for DC/DC



Dual N-Channel MOSFET

Ordering and Marking Information

 C2 G090ND06 XXXYWXXXXX	<p>Package Code C2: PDFN8L(5x6)</p> <p>Date Code XXXXWXXXXX</p>
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Note: HUAYI lead-free products contain molding compounds/die attach materials and 100% matte tin plate Termination finish; which are fully compliant with RoHS. HUAYI lead-free products meet or exceed the lead-free requirements of IPC/JEDEC J-STD-020 for MSL classification at lead-free peak reflow temperature. HUAYI defines "Green" to mean lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500ppm by weight).

HUAYI reserves the right to make changes, corrections, enhancements, modifications, and improvements to this product and/or to this document at any time without notice.

Absolute Maximum Ratings

Symbol	Parameter	Rating	Unit	
Common Ratings (Tc=25°C Unless Otherwise Noted)				
V _{DSS}	Drain-Source Voltage	60	V	
V _{GSS}	Gate-Source Voltage	±20	V	
T _J	Junction Temperature Range	-55 to 175	°C	
T _{STG}	Storage Temperature Range	-55 to 175	°C	
I _S	Source Current-Continuous(Body Diode)	Tc=25°C	56	A
Mounted on Large Heat Sink				
I _{DM}	Pulsed Drain Current *	Tc=25°C	220	A
I _D	Continuous Drain Current	Tc=25°C	56	A
		Tc=70°C	39.5	A
P _D	Maximum Power Dissipation	Tc=25°C	60	W
		Tc=70°C	30	W
R _{θJC}	Thermal Resistance, Junction-to-Case		2.5	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient		50	°C/W
EAS	SinglePulsed-			

Electrical Characteristics (Cont.) (Tc =25°C Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	HYG090ND06LS1			Unit
			Min	Typ.	Max	
Dynamic Characteristics						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz	-	2.1	-	Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =25V, Frequency=1.0MHz	-	926	-	pF
C _{oss}	Output Capacitance					
C _{rss}	Reverse Transfer Capacitance					
t _{d(ON)}	Turn-on Delay Time	V _{DD} =30V, R _G =4 I _{DS} =20A, V _{GS} =10V	-	7.7	-	ns
T _r	Turn-on Rise Time					
t _{d(OFF)}	Turn-off Delay Time					
T _f	Turn-off Fall Time					
Gate Charge Characteristics						
Q _g	Total Gate Charge V _{GS} =10V	V _{DS} =48V, V _{GS} =10V, I _D =20A	-	18.5	-	nC
Q _g	Total Gate Charge V _{GS} =4.5V)					
Q _{gs}	Gate-Source Charge					
Q _{gd}	Gate-Drain Charge					

Note: *Pulse test pulse width 300us duty cycle 2%

Typical Operating Characteristics

Figure 1: Power Dissipation

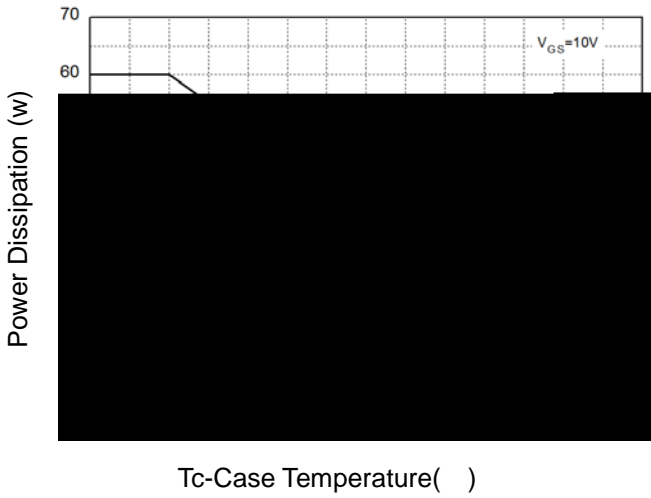


Figure 2: Drain Current

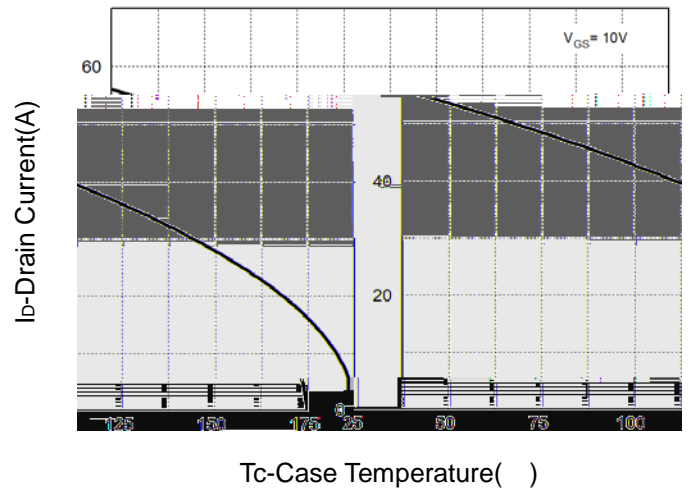


Figure 3: Safe Operation Area

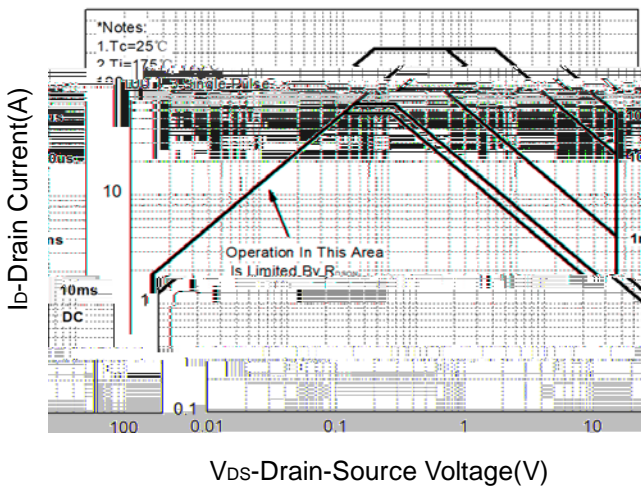


Figure 4: Thermal Transient Impedance

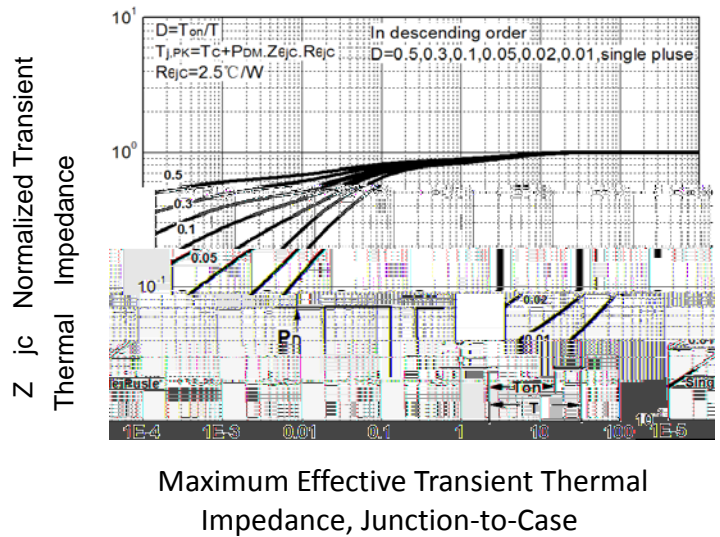


Figure 5: Output Characteristics

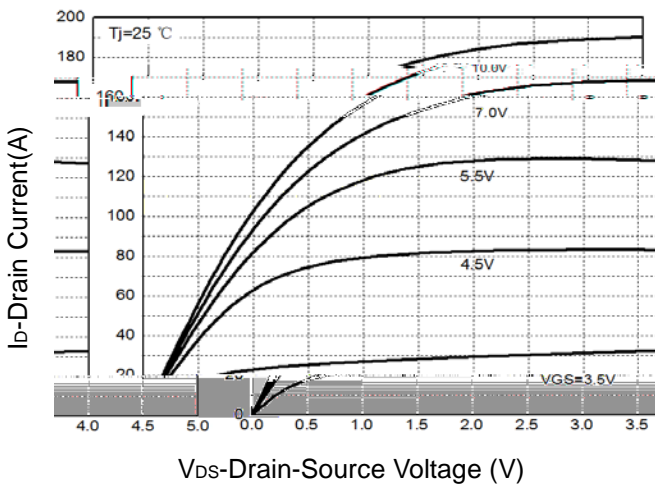
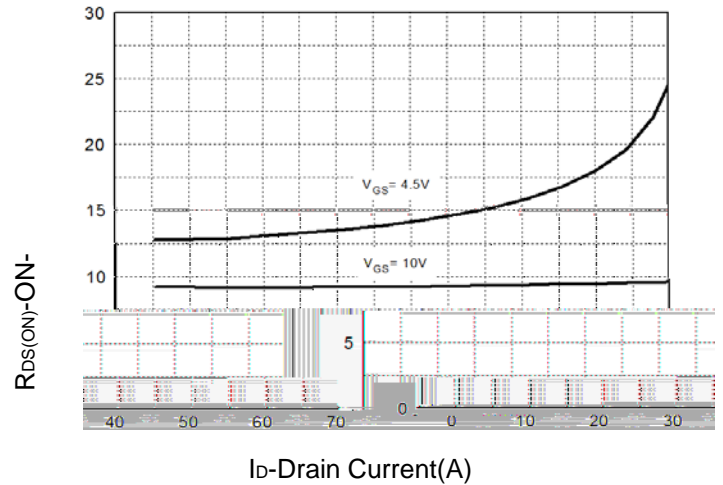
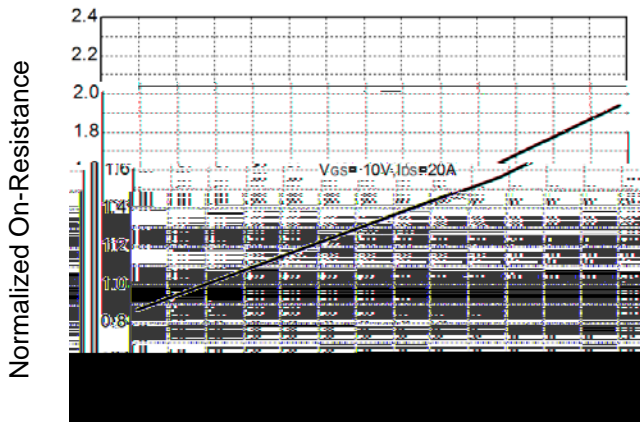


Figure 6: Drain-Source On Resistance



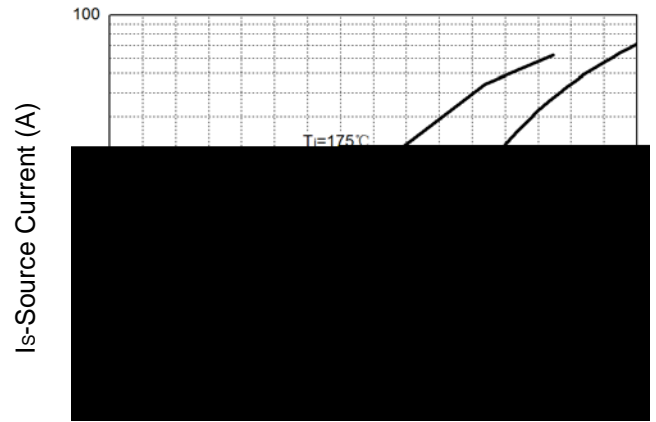
Typical Operating Characteristics

Figure 7: On-Resistance vs. Temperature



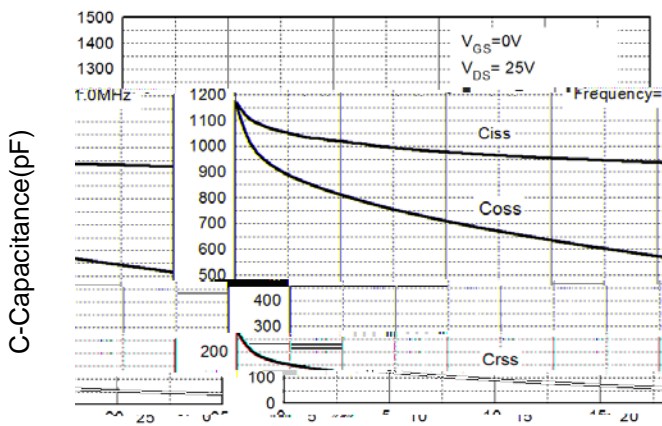
T_j-Junction Temperature (°C)

Figure 8: Source-Drain Diode Forward



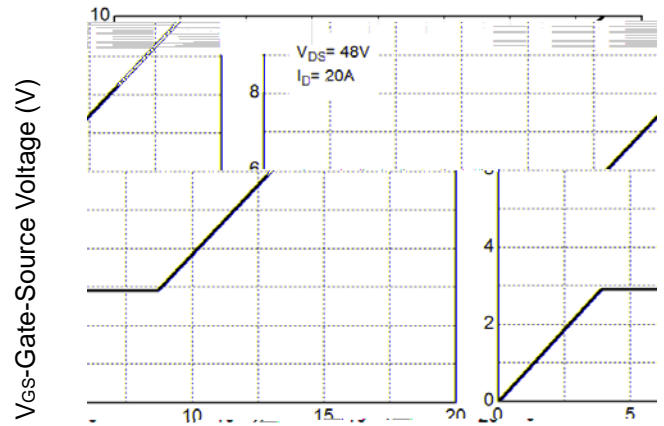
V_{SD}-Source-Drain Voltage(V)

Figure 9: Capacitance Characteristics



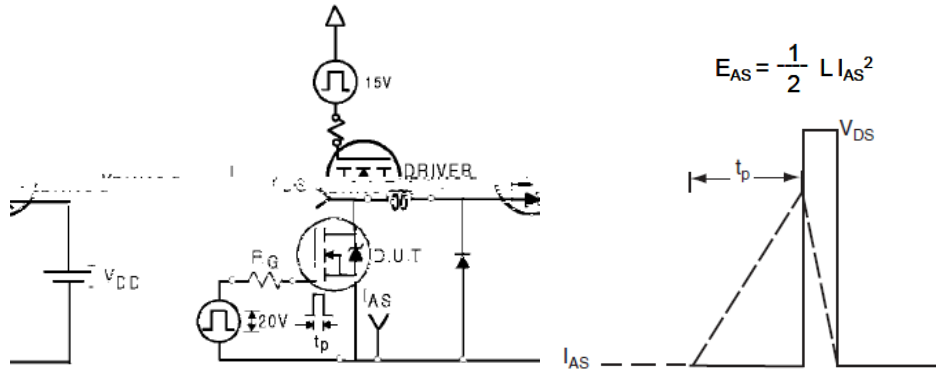
V_{DS}-Drain-Source Voltage (V)

Figure 10: Gate Charge Characteristics

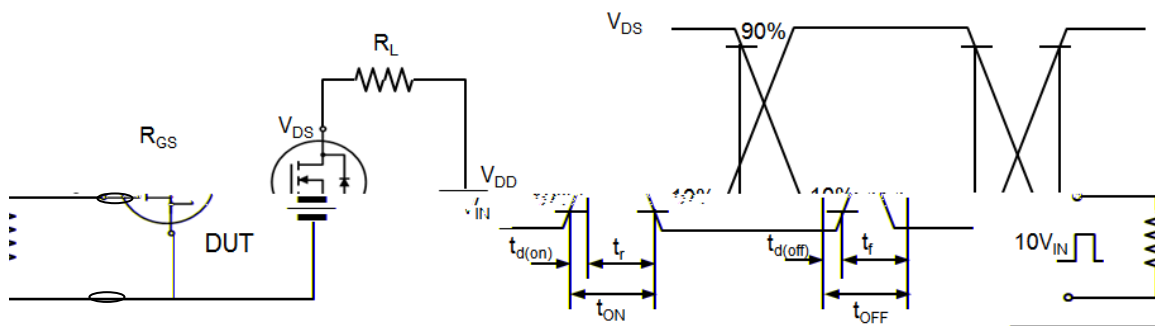


Q_G-Gate Charge (nC)

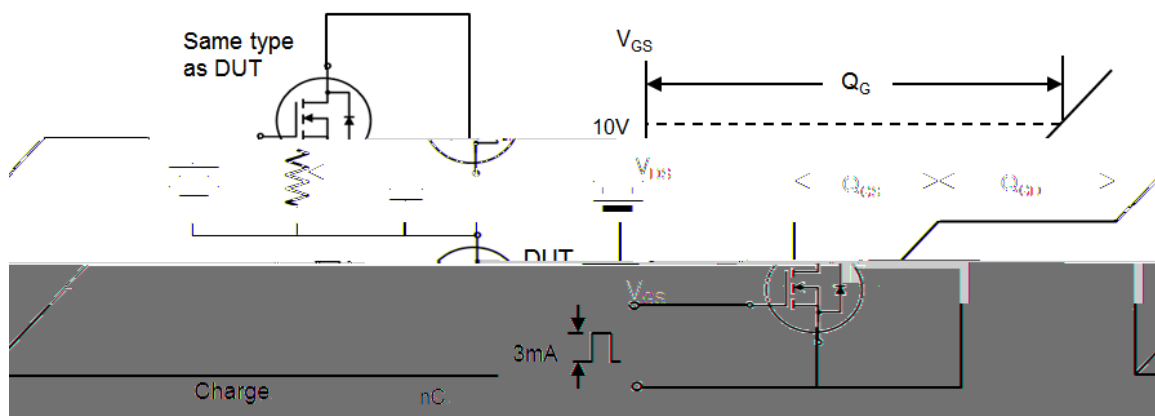
Avalanche Test Circuit



Switching Time Test Circuit



Gate Charge Test Circuit

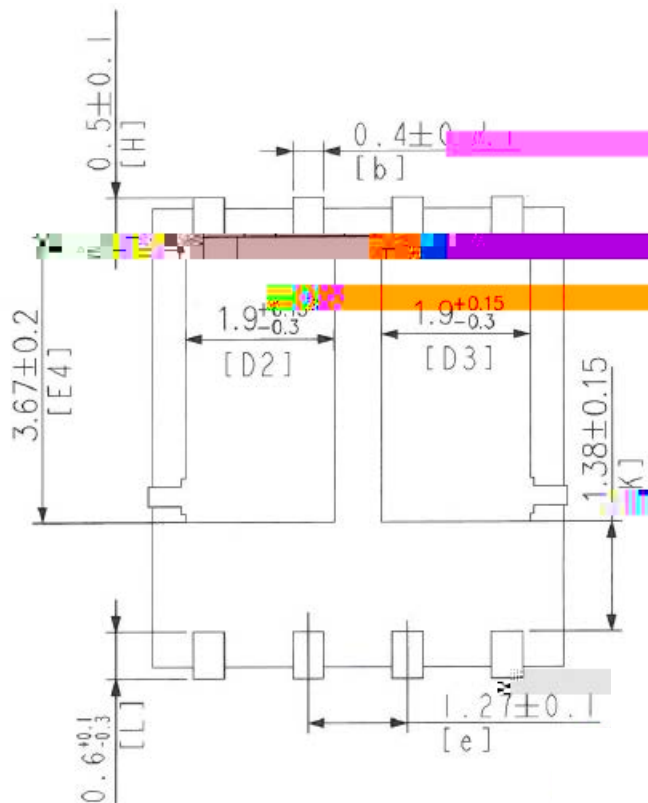
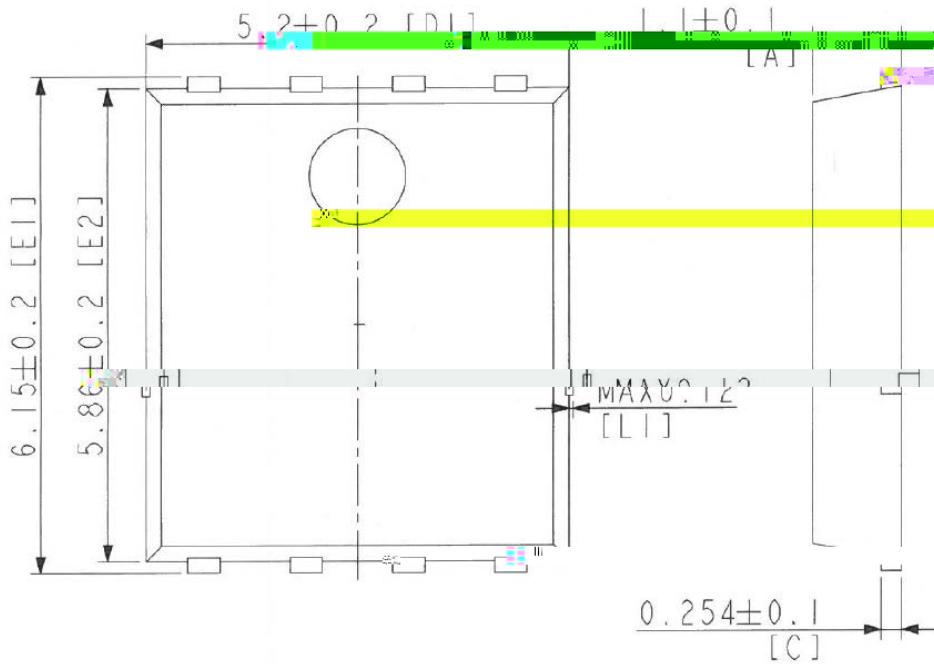


Device Per Unit

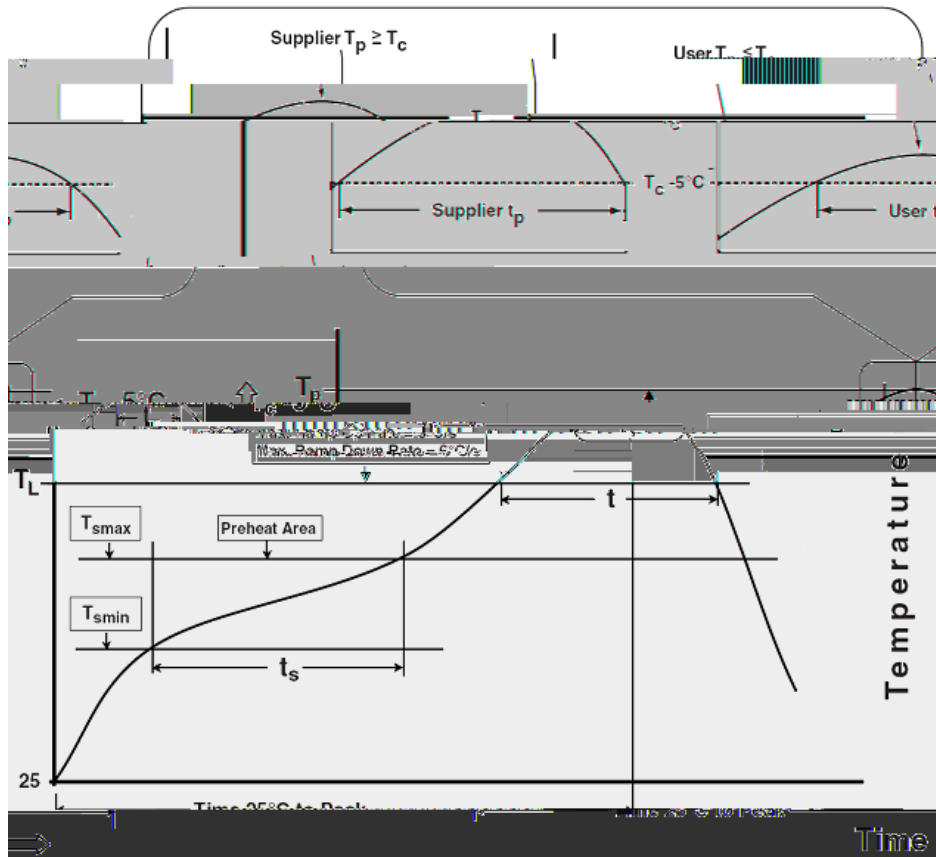
Package Type	Unit	Quantity
PDFN8L(5x6)	Reel	5000

Package Information

PDFN8L(5x6)



Classification Profile



Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Preheat & Soak		
Temperature min (T_{smin})	100 °C	150 °C
Temperature max (T_{smax})	150 °C	200 °C
Time (T_{smin} to T_{smax}) (t_s)	60-120 seconds	60-120 seconds
Average ramp-up rate (T_{smax} to T_P)	3 °C/second max.	3 °C/second max.
Liquidous temperature (T_L)	183 °C	217 °C
Time at liquidous (t_l)	60-150 seconds	60-150 seconds
Peak package body Temperature (T_p)*	See Classification Temp in table 1	See Classification Temp in table 2
Time (t_p)** within 5°C of the specified classification temperature (T_c)	20** seconds	30** seconds
Average ramp-down rate (T_p to T_{smax})	6 °C/second max.	6 °C/second max.
Time 25°C to peak temperature	6 minutes max.	8 minutes max.
*Tolerance for peak profile Temperature (T_p) is defined as a supplier minimum and a user maximum.		
** Tolerance for time at peak profile temperature (t_p) is defined as a supplier minimum and a user maximum.		

Table 1. SnPb Eutectic Process – Classification Temperatures (Tc)

Package Thickness	Volume mm <350	Volume mm 350
2.5 mm	235 °C	220 °C
	220 °C	220 °C

Table 2. Pb-free Process – Classification Temperatures (Tc)

Package Thickness	Volume mm <350	Volume mm 350-2000	Volume mm 2000
<1.6 mm	260 °C	260 °C	260 °C